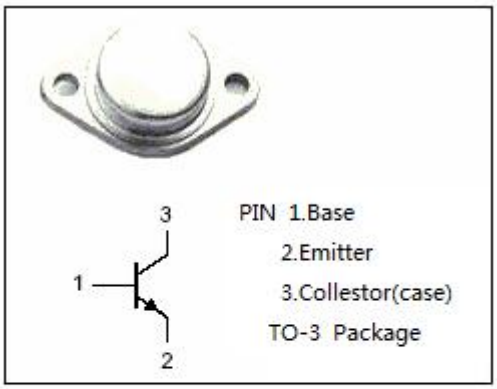
isc Silicon NPN Power Transistor — BUW25

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  :$V_{(BR)CEO}$= 400V(Min.)
- High Speed Switching
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

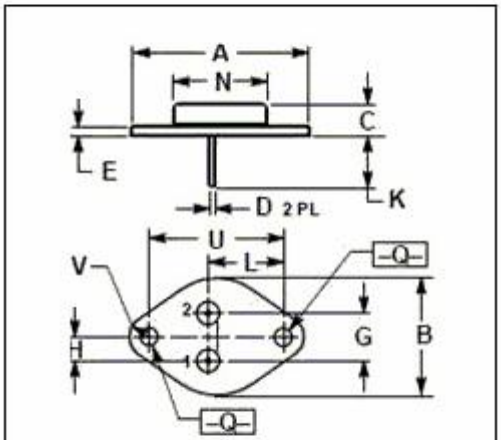


APPLICATIONS

- Designed for use in switching mode power supply.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	600	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	10	A
I_B	Base Current-Continuous	3	A
P_T	Total Power Dissipation @ T_C≤25℃	125	W
T_J	Junction Temperature	200	℃
T_{stg}	Storage Temperature Range	-65~200	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.25	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; I_B= 0	400			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2.5A; I_B= 0.5A			1.2	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 2.5A; I_B= 0.5A			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 600V; I_E= 0			0.1	mA
I_{EBO}	Emitter Cutoff current	V_{EB}=7V; I_C= 0			0.1	mA
h_{FE-1}	DC Current Gain	I_C= 1A; V_{CE}= 5V	15		40	
h_{FE-2}	DC Current Gain	I_C= 4A; V_{CE}= 5V	15			
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 10V		20		MHz